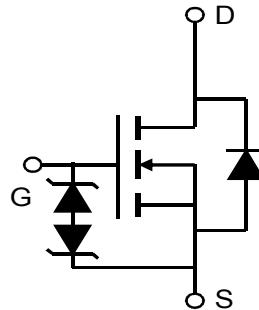


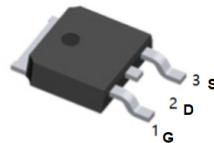
General Description

- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Eoss
- ESD protected
- RoHS and Halogen-Free Compliant



Product Summary

V_{DS}	60V
I_D (at $V_{GS}=10V$)	46A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 9.5mΩ
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 13.3mΩ



TO-252(DPAK) top view

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	46	A
$T_C=100^\circ C$		36.5	
Pulsed Drain Current ^C	I_{DM}	110	
Continuous Drain Current	I_{DSM}	19	A
$T_A=70^\circ C$		15	
Avalanche Current ^C	I_{AS}	17	A
Avalanche energy ^C	E_{AS}	43	mJ
V_{DS} Spike ^I	V_{SPIKE}	72	V
Power Dissipation ^B	P_D	59.5	W
$T_C=100^\circ C$		23.5	
Power Dissipation ^A	P_{DSM}	6.2	W
$T_A=70^\circ C$		4.0	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	15	20	°C/W	
Maximum Junction-to-Ambient ^{AD}		40	50	°C/W	
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1.7	2.1	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}, V_{GS}=0\text{V}$			1	μA
			$T_J=55^\circ\text{C}$		5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm20\text{V}$			±10	μA
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.4	1.8	2.4	V
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$		7.7	9.5	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=20\text{A}$		10.3	13.3	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=20\text{A}$		52		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.72	1	V
I_S	Maximum Body-Diode Continuous Current ^G				46	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=30\text{V}, f=1\text{MHz}$		1100		pF
C_{oss}	Output Capacitance			300		pF
C_{rss}	Reverse Transfer Capacitance			28		pF
R_g	Gate resistance	f=1MHz	0.6	1.2	2.0	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=30\text{V}, I_D=20\text{A}$		14.5	25	nC
$Q_g(4.5\text{V})$	Total Gate Charge			7	13	nC
Q_{gs}	Gate Source Charge			2.5		nC
Q_{gd}	Gate Drain Charge			3.5		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}, V_{DS}=30\text{V}, R_L=1.5\Omega, R_{GEN}=3\Omega$		6.5		ns
t_r	Turn-On Rise Time			3.5		ns
$t_{D(off)}$	Turn-Off DelayTime			22		ns
t_f	Turn-Off Fall Time			3		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}, di/dt=500\text{A}/\mu\text{s}$		19		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}, di/dt=500\text{A}/\mu\text{s}$		65		nC

A. The value of R_{JJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\text{JJA}} \leq 10\text{s}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature $T_{J(\text{MAX})}=150^\circ\text{C}$.

D. The R_{JJA} is the sum of the thermal impedance from junction to case R_{JJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

I. The spike duty cycle 5% max, limited by junction temperature $T_J(\text{MAX})=125^\circ\text{C}$.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

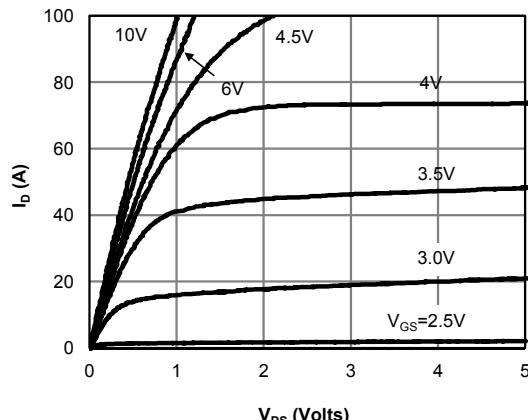


Figure 1: On-Region Characteristics (Note E)

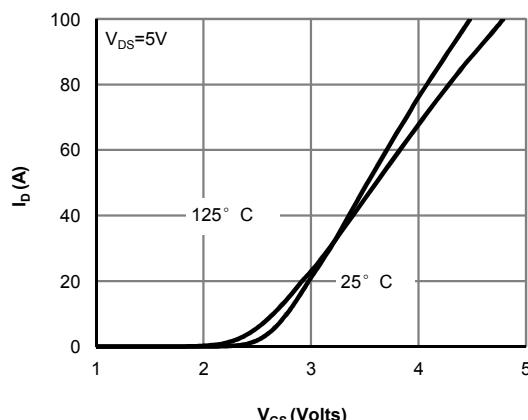


Figure 2: Transfer Characteristics (Note E)

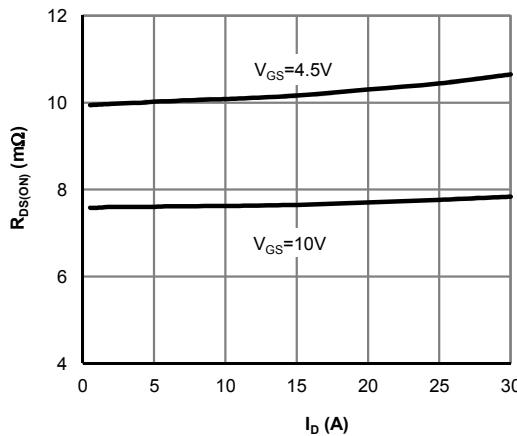
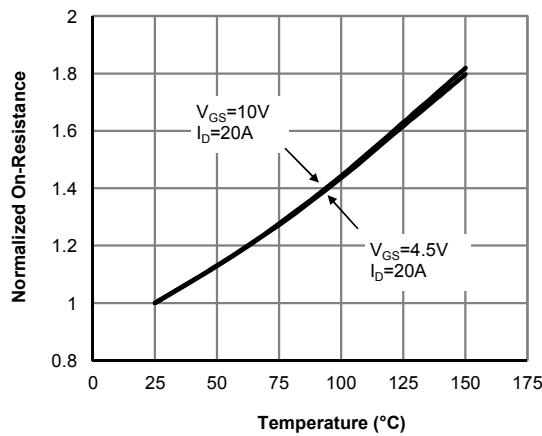
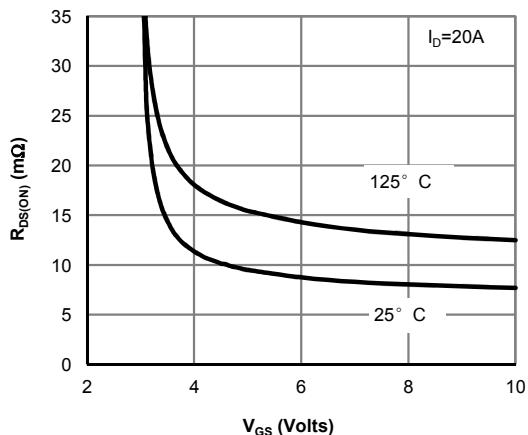


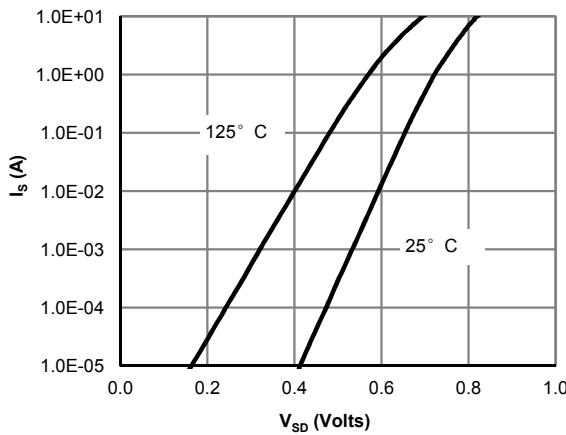
Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)



**Figure 4: On-Resistance vs. Junction Temperature
(Note E)**



**Figure 5: On-Resistance vs. Gate-Source Voltage
(Note E)**



**Figure 6: Body-Diode Characteristics
(Note E)**

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

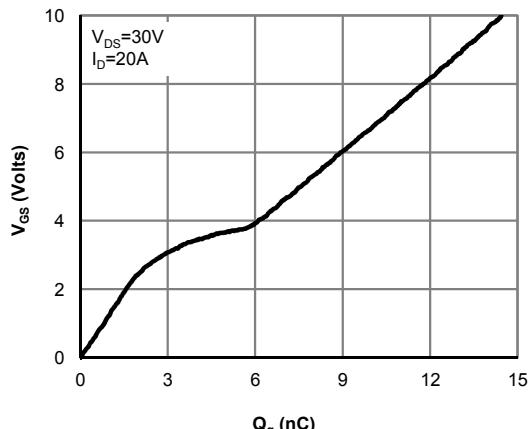


Figure 7: Gate-Charge Characteristics

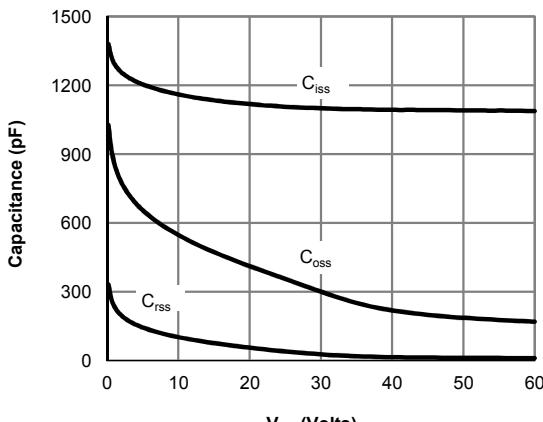


Figure 8: Capacitance Characteristics

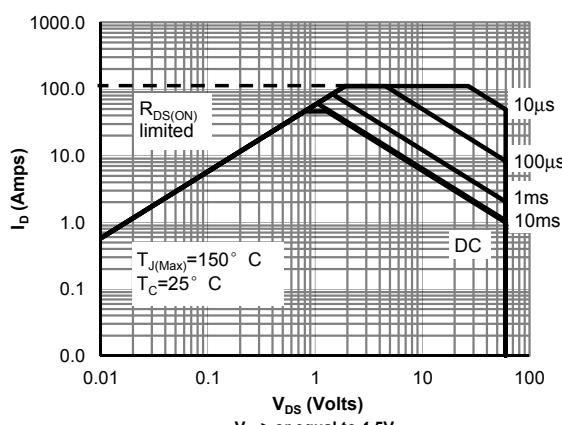


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

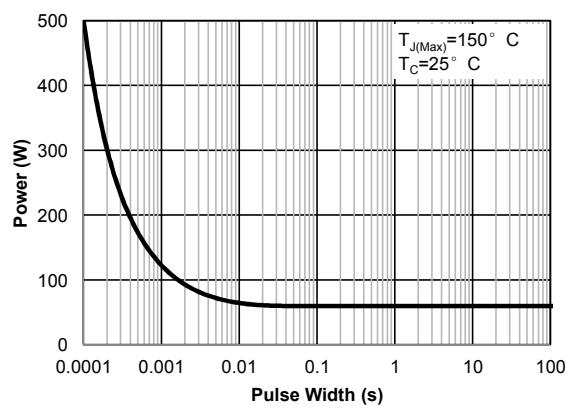


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

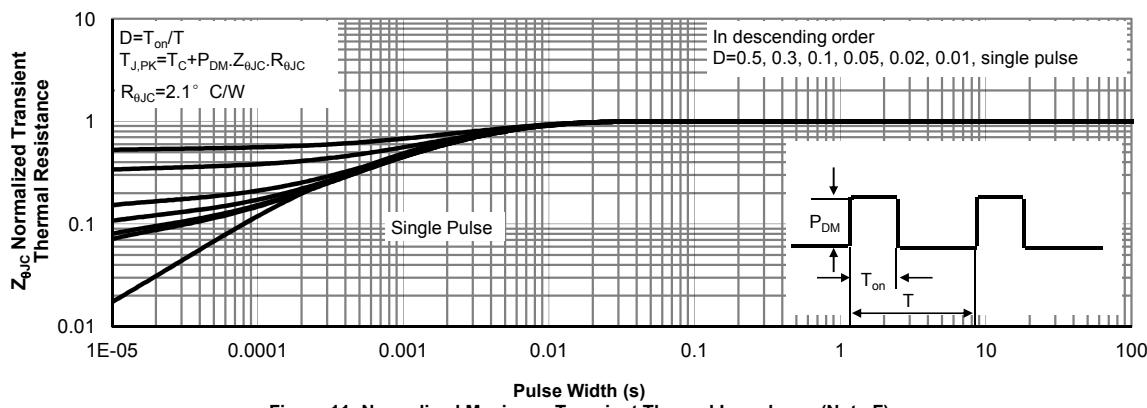


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

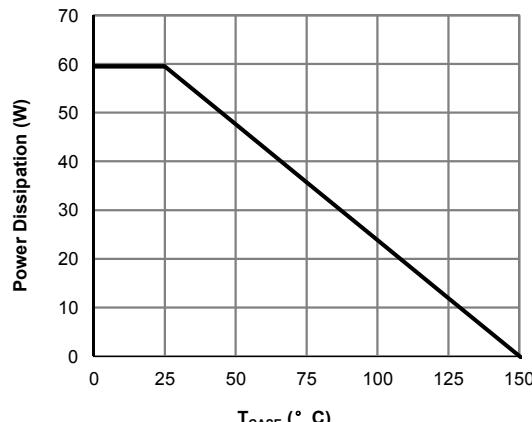


Figure 12: Power De-rating (Note F)

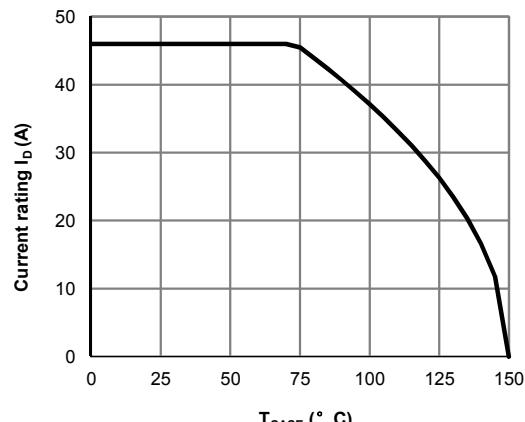


Figure 13: Current De-rating (Note F)

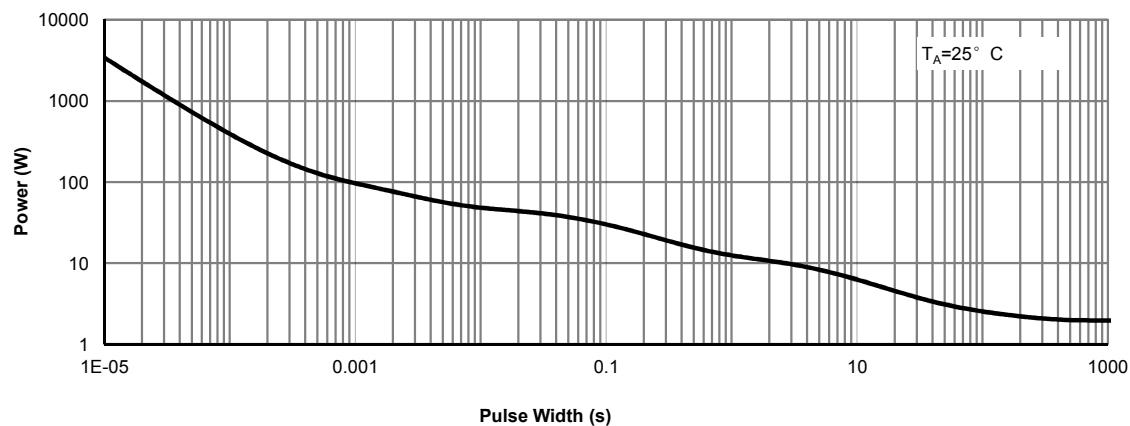


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

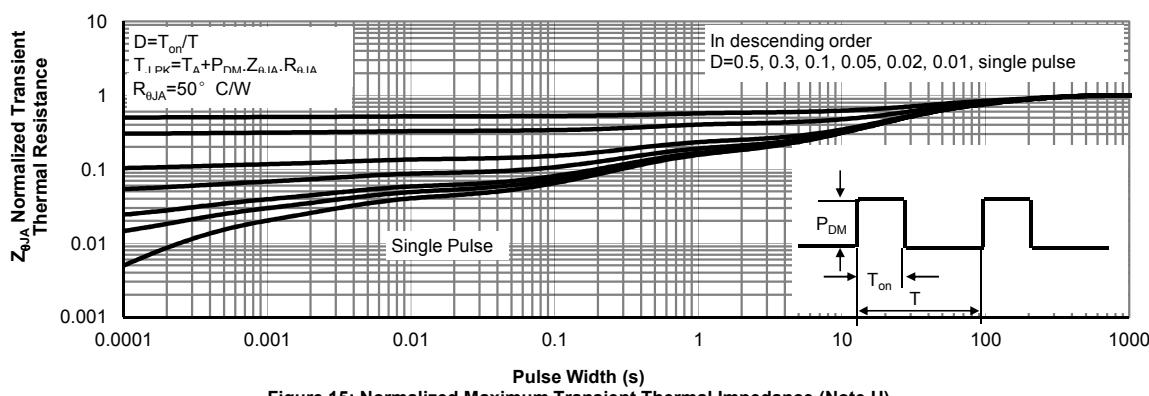


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

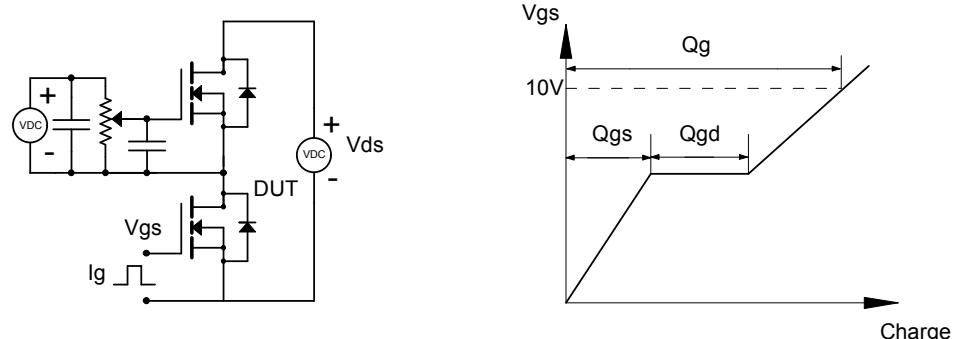


Figure B: Resistive Switching Test Circuit & Waveforms

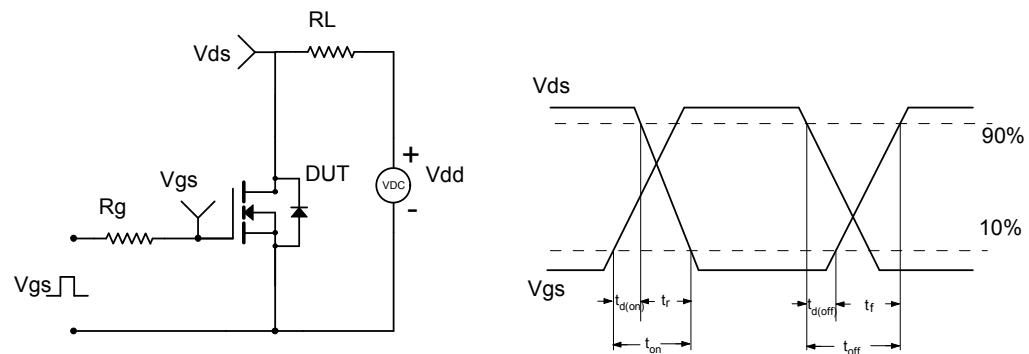


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

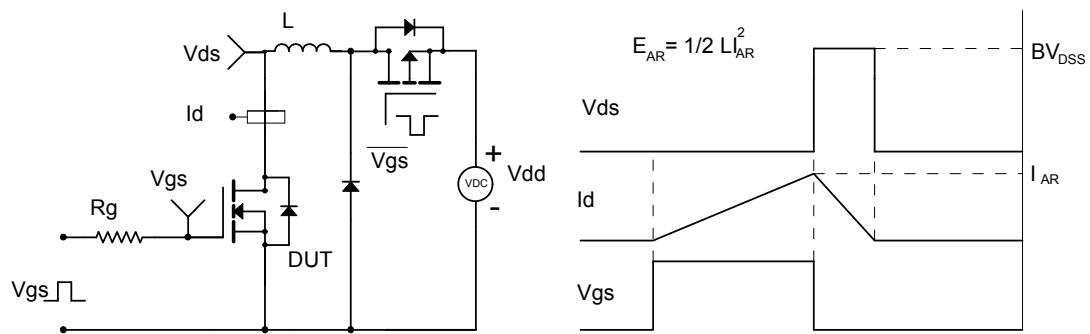
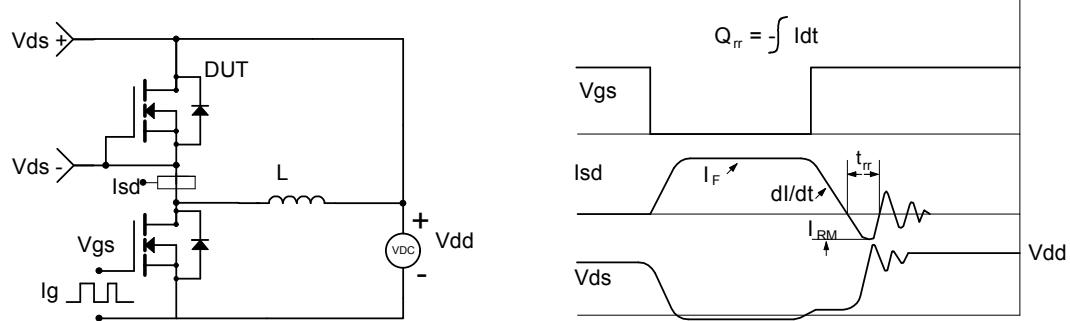
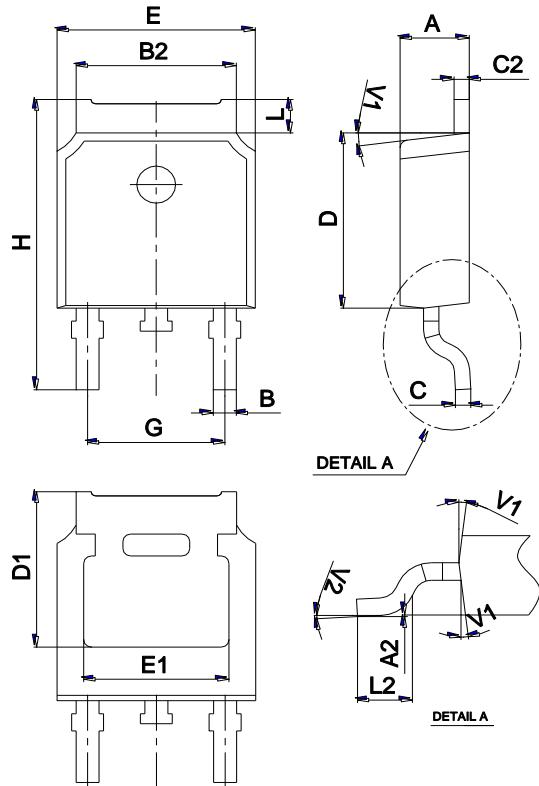


Figure D: Diode Recovery Test Circuit & Waveforms



Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
Min.	Typ.	Max.	Min.	Typ.	Max.	
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Ordering information

Order code	Package	Baseqty	Delivery mode
AOD2610E	TO-252	2500	Tape and reel